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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/808,422	03/25/2004	Masanobu Senda	PTGF-03093	6952
21254	7590	11/25/2005	EXAMINER	
MCGINN INTELLECTUAL PROPERTY LAW GROUP, PLLC 8321 OLD COURTHOUSE ROAD SUITE 200 VIENNA, VA 22182-3817			MENZ, DOUGLAS M	
		ART UNIT	PAPER NUMBER	
			2891	

DATE MAILED: 11/25/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/808,422	SENDA ET AL.	
	Examiner	Art Unit	
	Douglas M. Menz	2891	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 09 September 2005.
 2a) This action is FINAL. 2b) This action is non-final.
 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 1-16 is/are pending in the application.
 4a) Of the above claim(s) 9-16 is/are withdrawn from consideration.
 5) Claim(s) _____ is/are allowed.
 6) Claim(s) 1-8 is/are rejected.
 7) Claim(s) _____ is/are objected to.
 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.
 10) The drawing(s) filed on 25 March 2004 is/are: a) accepted or b) objected to by the Examiner.
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 a) All b) Some * c) None of:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892)
 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)
 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
 Paper No(s)/Mail Date 3/25/04.

4) Interview Summary (PTO-413)
 Paper No(s)/Mail Date. _____.
 5) Notice of Informal Patent Application (PTO-152)
 6) Other: Search History.

DETAILED ACTION

Election/Restrictions

Applicant's election without traverse of Group I, claims 1-8, in the reply filed on 9/9/05 is acknowledged.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1-8 are rejected under 35 U.S.C. 102(e) as being anticipated by Tanabe et al. (US 6469320).

Regarding claim 1, Tanabe discloses a semiconductor light-emitting element (Fig. 1) that is made by using the lateral growth function of semiconductor crystal while providing an ELO mask (3, Figs. 1-2) on a crystal growth surface of a crystal growth substrate, wherein at least part of a sidewall (3a, Figs. 1-2) of the ELO mask is provided with an inclined plane that is inclined to the crystal growth surface such that the

semiconductor crystal to be formed on the ELO mask substantially has no void (Figs. 1-2 and Cols. 7-8).

Regarding claim 2, Tanabe further discloses wherein at least part of the inclined plane is curved (3, Fig. 2 *note: realization of mask 3 would incur rounded or curved portions of the inclined sidewall due to standard semiconductor etching processes*)

Regarding claim 3, Tanabe further discloses wherein the shape of ELO mask (3, Fig. 2) in cross section vertical to the crystal growth surface is formed nearly semicircular, nearly semi-elliptic or partially either of these shapes (Fig. 2).

Regarding claim 4, Tanabe further discloses wherein the shape of ELO mask (3, Fig. 2) in cross section vertical to the crystal growth surface is formed nearly isosceles triangular or nearly isosceles trapezoidal with flat top (Fig. 2).

Regarding claim 5, Tanabe further discloses wherein the shape of ELO mask on the crystal growth surface is formed like a spot or a nearly stripe (Figs. 6-8).

Regarding claim 6, Tanabe further discloses wherein the crystal growth substrate is of sapphire (Col. 7, lines 55-60).

Regarding claim 7, Tanabe further discloses wherein the semiconductor crystal is of $\text{Al}_x\text{Ga}_{1-x}\text{N}$, x from 0-1(Col. 9).

Regarding claim 8, Tanabe further discloses wherein: the semiconductor light emitting element is a flip-chip type LED (Col. 1, lines: 5-20) the refractive index of the ELO mask is set to be greater than that of the crystal growth substrate and smaller than that of the semiconductor crystal (Cols. 7-8, *material properties*).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas M. Menz whose telephone number is 571-272-1877. The examiner can normally be reached on M-F 8-5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Bill Baumeister can be reached on 571-272-1722. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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